



TR 2N6107(=BDP286);TO220;tranzystor PNP;7A;70V;40W;>5MHz;RoHS



Dane techniczne:

Nazwa: 2N6107(=BDP286)

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 7A

Napięcie kolektor-emiter: 70V

Moc: 40W

Częstotliwość: >5MHz

Obudowa: TO220

Montaż: przewlekany (THT)



Complementary Silicon Power Transistors

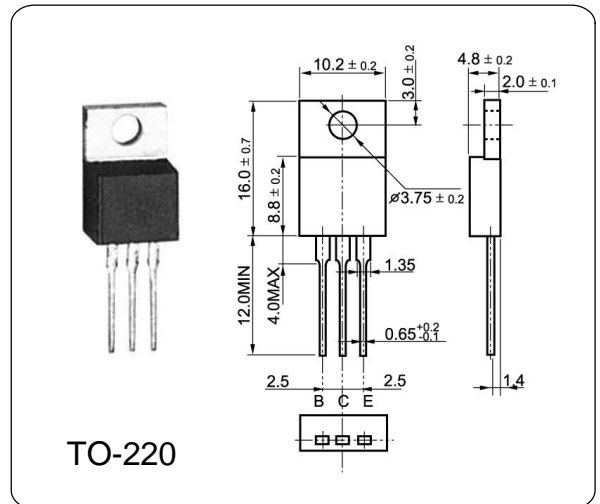
2N6292 / 2N6107

DESCRIPTION

It is intended for use in power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	70	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	7.0	A
Base Current	I_B	3.0	A
Total Dissipation at	P_{tot}	40	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	$V_{CB}=60V, I_E=0$	—	—	0.3	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	1.0	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=10mA, I_B=0$	70	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=4V, I_C=2.0A$	30	—	150	
	$h_{FE(2)}$	$V_{CE}=4V, I_C=7.0A$	2.3	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=7.0A, I_B=3.0A$	—	—	3.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=4V, I_C=7.0A$	—	—	3.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=4.0V, I_C=500mA$	4.0	—	—	MHz